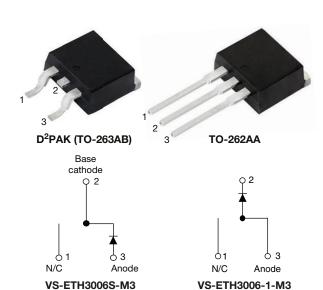


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Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS						
I _{F(AV)}	30 A					
V _R	600 V					
V _F at I _F	1.4 V					
t _{rr} (typ.)	27 ns					
T _J max.	175 °C					
Package	D ² PAK (TO-263AB), TO-262AA					
Circuit configuration	Single					

FEATURES

- Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current



- Designed and qualified according to JEDEC®-JESD 47
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION/APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Repetitive peak reverse voltage	V_{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 95 °C	30	۸			
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	180	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-		
Forward voltage	V _F	I _F = 30 A	ı	2.0	2.65	V	
r orward vortage	V F	I _F = 30 A, T _J = 150 °C	ı	1.4	1.8		
Reverse leakage current		$V_R = V_R$ rated	-	0.02	30	μA	
neverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	50	300	μΑ	
Junction capacitance	C _T	V _R = 600 V	-	20	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

VS-ETH3006S-M3, VS-ETH3006-1-M3

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	AMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX.								
		$I_F = 1 A, dI_F/dt = 50$	0 A/μs, V _R = 30 V	-	26	35			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	26	-	ns		
		T _J = 125 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 200 \text{ V}$	-	70	-			
Dools we cover a comment	I _{RRM}	T _J = 25 °C		-	3.5	-	Α		
Peak recovery current		T _J = 125 °C		-	7.6	-			
Reverse recovery charge	0	T _J = 25 °C] ''	-	50	-			
	Q _{rr}	T _J = 125 °C		-	280	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction-to-case	R _{thJC}		i	0.95	1.4	°C/W	
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	70		
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-		
Weight			-	2.0	-	g	
vveigni			-	0.07	-	OZ.	
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)	
Madding daying		Case style D ² PAK (TO-263AB) ETH3006S			3006S		
Marking device		Case style TO-262AA	ETH3006-1				

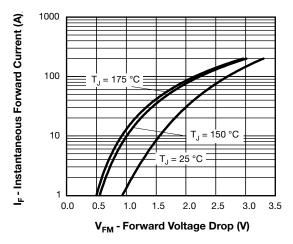


Fig. 1 - Typical Forward Voltage Drop Characteristics

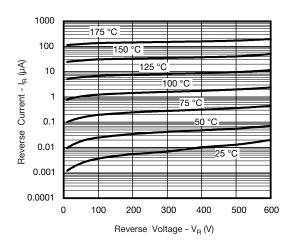


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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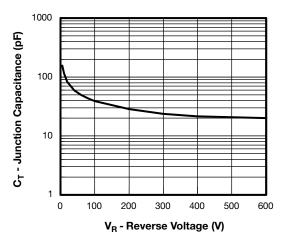


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

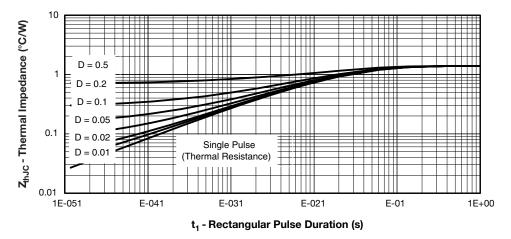


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

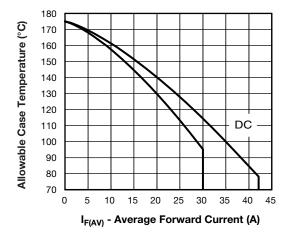


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

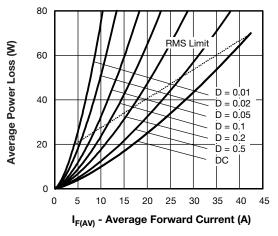


Fig. 6 - Forward Power Loss Characteristics

t_{rr} (ns)

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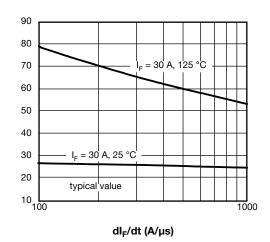


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

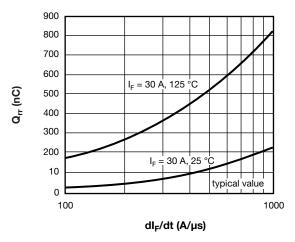
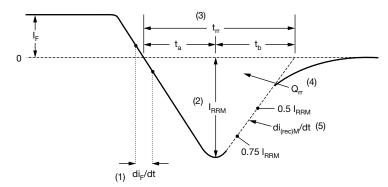


Fig. 8 - Typical Stored Charge vs. dl_E/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{F}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

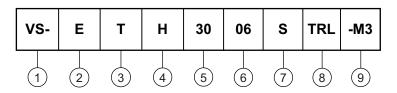
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-ETH3006S-M3, VS-ETH3006-1-M3

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ORDERING INFORMATION TABLE

Device code



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Circuit configuration

E = single

T = TO-220

4 5 H = hyperfast recovery time

Current code (30 = 30 A)

Voltage code (06 = 600 V)

• $S = D^2PAK (TO-263AB)$

• -1 = TO-262AA

8 • None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK (TO-263AB) package)

• TRR = tape and reel (right oriented, for D²PAK (TO-263AB) package)

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free 9

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-ETH3006S-M3	50	Antistatic plastic tubes				
VS-ETH3006STRR-M3	800	13" diameter plastic tape and reel				
VS-ETH3006STRL-M3	800	13" diameter plastic tape and reel				
VS-ETH3006-1-M3	50	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Diffiersions	TO-262AA	www.vishay.com/doc?96165				
Dout more information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444				
Part marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424				



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES		SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches

Modified JEDEC® outline TO-262







⊕ 0.010 **M** A**M** B

Lead assignments



Diodes 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	IETERS	INC	NOTES				
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES			
Α	4.06	4.83	0.160	0.190				
A1	2.03	3.02	0.080	0.119				
b	0.51	0.99	0.020	0.039				
b1	0.51	0.89	0.020	0.035	4			
b2	1.14	1.78	0.045	0.070				
b3	1.14	1.73	0.045	0.068	4			
С	0.38	0.74	0.015	0.029				
c1	0.38	0.58	0.015	0.023	4			
c2	1.14	1.65	0.045	0.065				
D	8.51	9.65	0.335	0.380	2			
D1	6.86	8.00	0.270	0.315	3			
E	9.65	10.67	0.380	0.420	2, 3			
E1	7.90	8.80	0.311	0.346	3			
е	2.54	BSC	0.100) BSC				
L	13.46	14.10	0.530	0.555				
L1	-	1.65	-	0.065	3			
L2	3.56	3.71	0.140	0.146				

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
 (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- Controlling dimension: inches
- Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



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